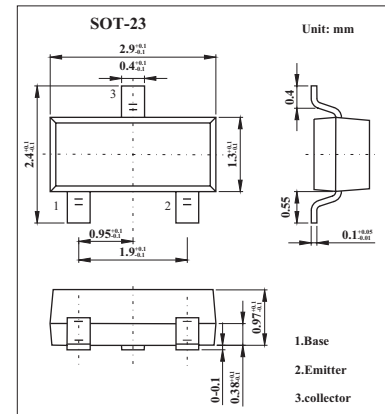


## Silicon NPN Epitaxial Planar Type

## 2SC3547A



### ■ Features

- Transition frequency is high and dependent on current excellently.

### ■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V <sub>CB0</sub>	20	V
Collector-emitter voltage	V <sub>CEO</sub>	12	V
Emitter-base voltage	V <sub>EBO</sub>	3	V
Base current	I <sub>B</sub>	15	mA
Collector current	I <sub>C</sub>	30	mA
Collector power dissipation	P <sub>C</sub>	150	mW
Junction temperature	T <sub>J</sub>	125	°C
Storage temperature range	T <sub>stg</sub>	-55 to +125	°C

### ■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> = 10 V, I <sub>E</sub> = 0			0.1	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = 1 V, I <sub>C</sub> = 0			1.0	μA
Collector-emitter breakdown voltage	V <sub>(BR) CEO</sub>	I <sub>C</sub> = 1 mA, I <sub>B</sub> = 0	12			V
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> = 10 V, I <sub>C</sub> = 5 mA	35		130	
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> = 10 V, I <sub>C</sub> = 10 mA	3	4		GHz
Output capacitance	C <sub>ob</sub>	V <sub>CB</sub> = 10 V, I <sub>E</sub> = 0, f = 1 MHz		1.05	1.35	pF
Collector-base time constant	C <sub>cFrb</sub>	V <sub>CB</sub> = 10 V, I <sub>C</sub> = 5 mA, f = 30 MHz		4.5	10	ps

### ■ Marking

Marking	HI